

Standard Rectifier Module

$$V_{RRM} = 2 \times 1600 \text{ V}$$

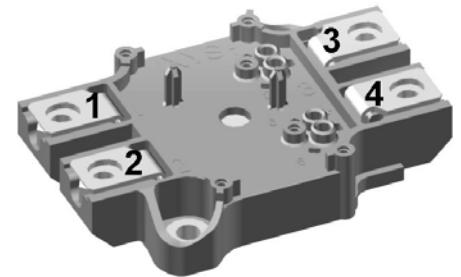
$$I_{FAV} = 200 \text{ A}$$

$$V_F = 1.06 \text{ V}$$

Phase leg

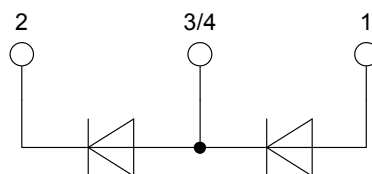
Part number

MDMA200P1600SA



Backside: isolated

 E72873



Features / Advantages:

- Planar passivated chips
- Very low leakage current
- Very low forward voltage drop
- Improved thermal behaviour

Applications:

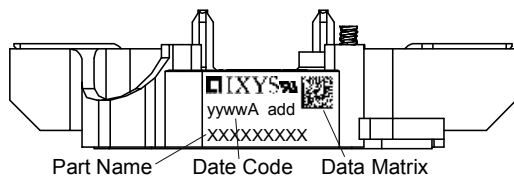
- Diode for main rectification
- For single and three phase bridge configurations

Package: SimBus A

- Isolation Voltage: 4800 V~
- Industry standard outline
- RoHS compliant
- Gate: Spring contacts for solder-free PCB-mounting
- Height: 17 mm
- Base plate: Copper internally DCB isolated
- Advanced power cycling

Rectifier				Ratings			
Symbol	Definition	Conditions		min.	typ.	max.	Unit
V_{RSM}	max. non-repetitive reverse blocking voltage	$T_{VJ} = 25^{\circ}\text{C}$				1700	V
V_{RRM}	max. repetitive reverse blocking voltage	$T_{VJ} = 25^{\circ}\text{C}$				1600	V
I_R	reverse current	$V_R = 1600\text{ V}$	$T_{VJ} = 25^{\circ}\text{C}$			200	μA
		$V_R = 1600\text{ V}$	$T_{VJ} = 150^{\circ}\text{C}$			15	mA
V_F	forward voltage drop	$I_F = 200\text{ A}$	$T_{VJ} = 25^{\circ}\text{C}$			1.13	V
		$I_F = 400\text{ A}$				1.33	V
		$I_F = 200\text{ A}$	$T_{VJ} = 125^{\circ}\text{C}$			1.06	V
		$I_F = 400\text{ A}$				1.32	V
I_{FAV}	average forward current	$T_C = 110^{\circ}\text{C}$ rectangular $d = 0.5$	$T_{VJ} = 150^{\circ}\text{C}$			200	A
V_{FO}	threshold voltage	} for power loss calculation only		$T_{VJ} = 150^{\circ}\text{C}$		0.76	V
r_F	slope resistance					1.4	m Ω
R_{thJC}	thermal resistance junction to case					0.15	K/W
R_{thCH}	thermal resistance case to heatsink				0.08		K/W
P_{tot}	total power dissipation	$T_C = 25^{\circ}\text{C}$				830	W
I_{FSM}	max. forward surge current	$t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}$	$T_{VJ} = 45^{\circ}\text{C}$			6.00	kA
		$t = 8,3\text{ ms}; (60\text{ Hz}), \text{ sine}$	$V_R = 0\text{ V}$			6.48	kA
		$t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}$	$T_{VJ} = 150^{\circ}\text{C}$			5.10	kA
		$t = 8,3\text{ ms}; (60\text{ Hz}), \text{ sine}$	$V_R = 0\text{ V}$			5.51	kA
I^2t	value for fusing	$t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}$	$T_{VJ} = 45^{\circ}\text{C}$			180.0	kA ² s
		$t = 8,3\text{ ms}; (60\text{ Hz}), \text{ sine}$	$V_R = 0\text{ V}$			174.7	kA ² s
		$t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}$	$T_{VJ} = 150^{\circ}\text{C}$			130.1	kA ² s
		$t = 8,3\text{ ms}; (60\text{ Hz}), \text{ sine}$	$V_R = 0\text{ V}$			126.3	kA ² s
C_J	junction capacitance	$V_R = 400\text{ V}; f = 1\text{ MHz}$			273		pF

Package SimBus A				Ratings			
Symbol	Definition	Conditions		min.	typ.	max.	Unit
I_{RMS}	RMS current	per terminal				300	A
T_{VJ}	virtual junction temperature			-40		150	°C
T_{op}	operation temperature			-40		125	°C
T_{stg}	storage temperature			-40		125	°C
Weight					152		g
M_D	mounting torque			3		5	Nm
M_T	terminal torque			2.5		5	Nm
$d_{Spp/App}$	creepage distance on surface striking distance through air	terminal to terminal	14.0	10.0			mm
$d_{Spb/Apb}$		terminal to backside	14.0	10.0			mm
V_{ISOL}	isolation voltage	t = 1 second	50/60 Hz, RMS; $I_{ISOL} \leq 1$ mA	4800			V
		t = 1 minute		4000			V



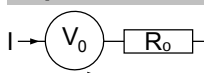
Part number

M = Module
 D = Diode
 M = Standard Rectifier
 A = (up to 1800V)
 200 = Current Rating [A]
 P = Phase leg
 1600 = Reverse Voltage [V]
 SA = SimBus A

Ordering	Part Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	MDMA200P1600SA	MDMA200P1600SA	Blister	9	510373

Equivalent Circuits for Simulation

* on die level

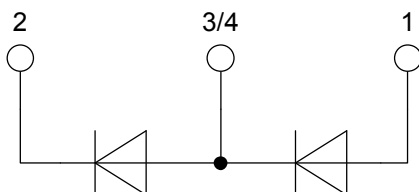
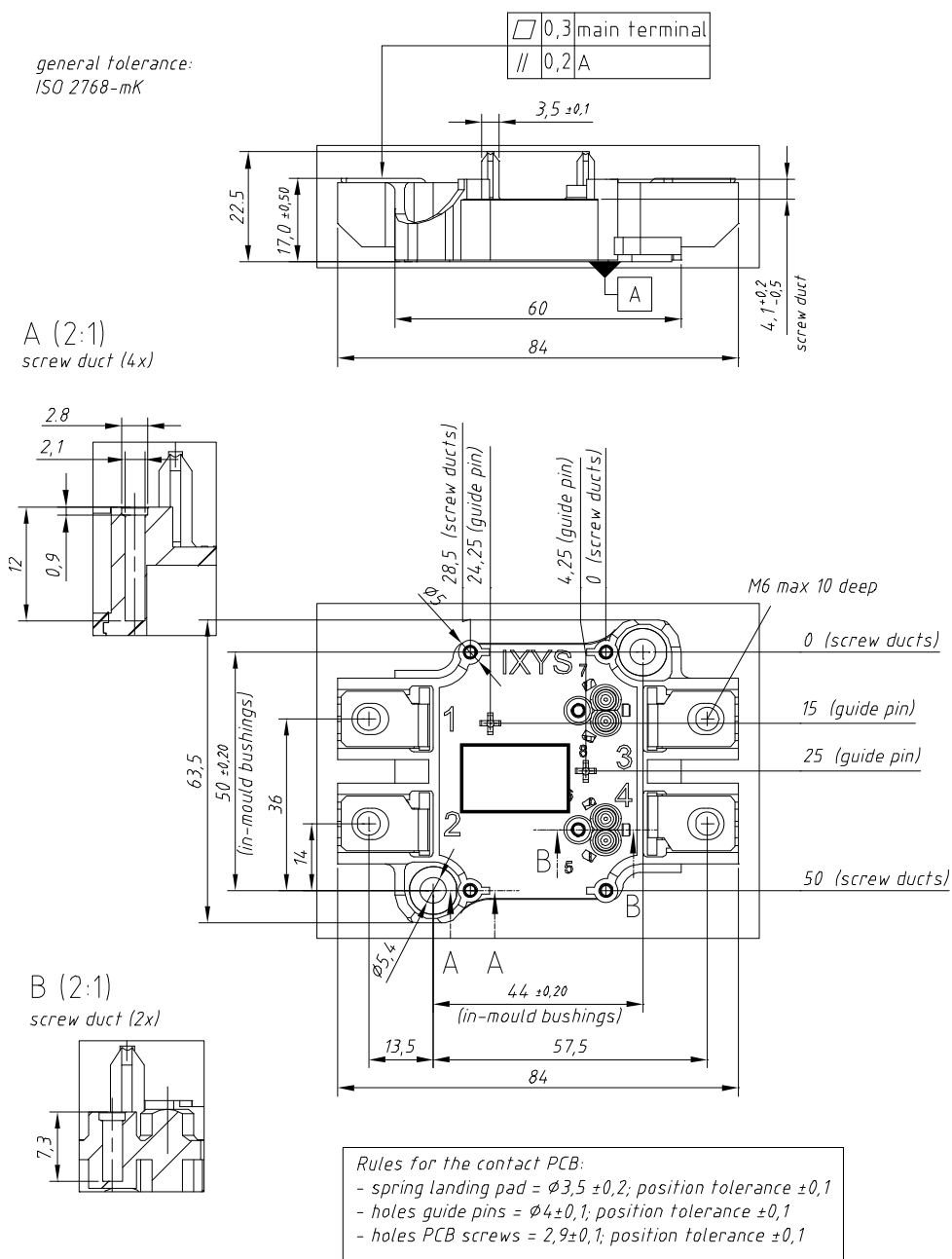
 $T_{VJ} = 150^\circ\text{C}$ 

Rectifier

$V_{0\max}$	threshold voltage	0.76	V
$R_{0\max}$	slope resistance *	0.8	mΩ

Outlines SimBus A

general tolerance:
ISO 2768-mK



Rectifier

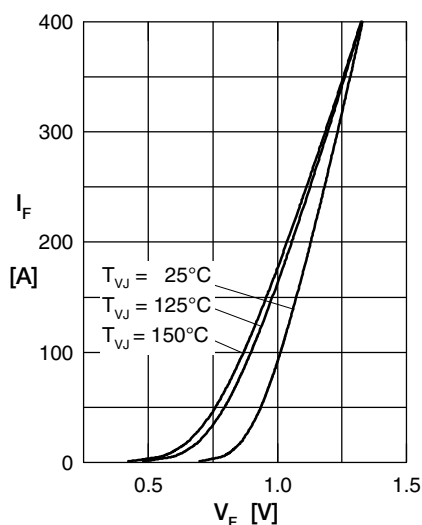


Fig. 1 Forward current versus voltage drop per diode

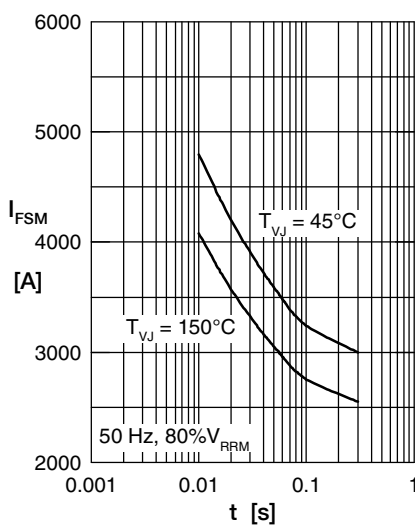


Fig. 2 Surge overload current vs. time per diode

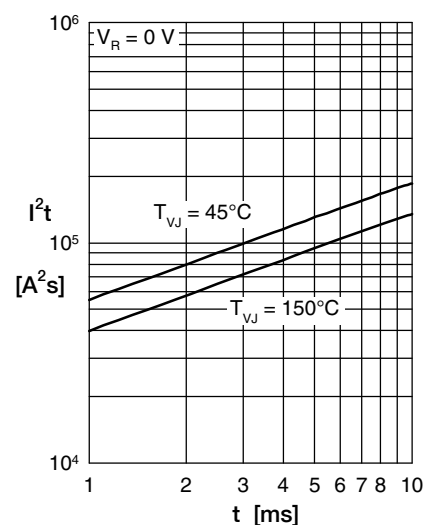


Fig. 3 I^2t versus time per diode

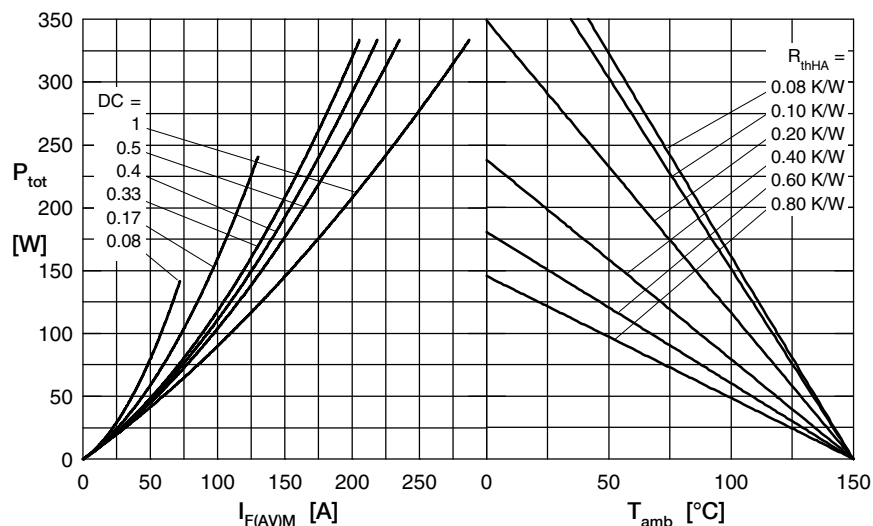


Fig. 4 Power dissipation vs. forward current and ambient temperature per diode

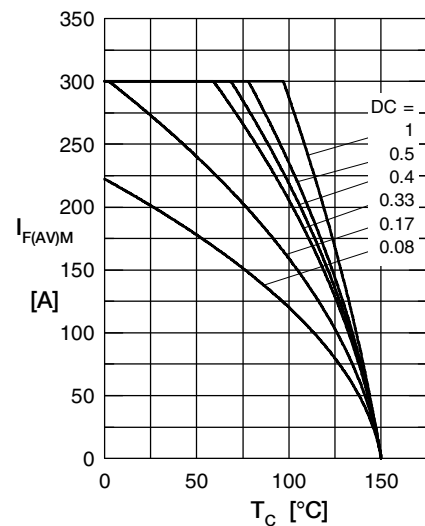


Fig. 5 Max. forward current vs. case temperature per diode

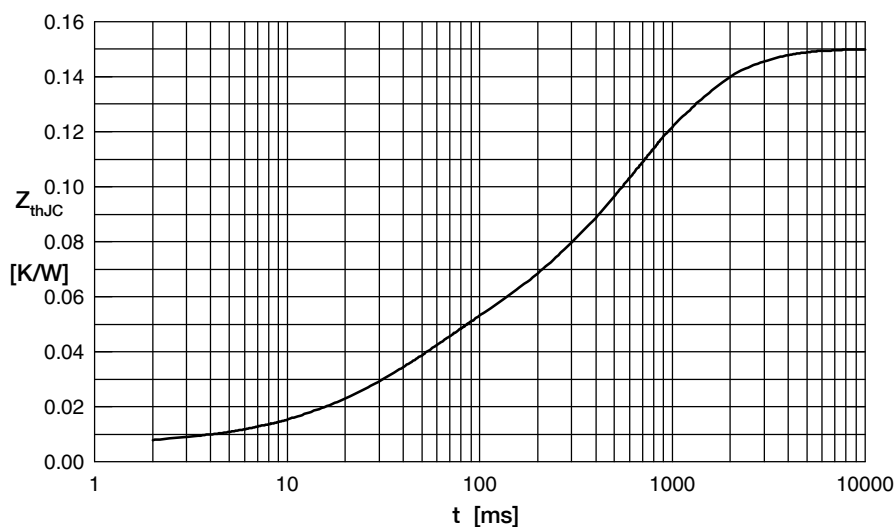


Fig. 6 Transient thermal impedance junction to case vs. time per diode

Constants for Z_{thJC} calculation:

i	R_{thi} (K/W)	t_i (s)
1	0.006	0.0005
2	0.035	0.0400
3	0.079	0.5500
4	0.030	1.5000

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